

SANYO

No. 1727B

2SB1123/2SD1623

PNP/NPN Epitaxial Planar Silicon Transistors

High-Current Switching Applications

Applications

- . Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- . Adoption of FBET, MBIT processes.
- . Low collector-to-emitter saturation voltage.
- . Large current capacity and wide ASO.
- . Fast switching speed.
- . Very small size making it easy to provide high-density, small-sized hybrid IC's.

(): 2SB1123

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)2	A
Collector Current(Pulse)	I_{CP}	(-)4	A
Collector Dissipation	P_C	500	mW
	P_C (Note)	1.3	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

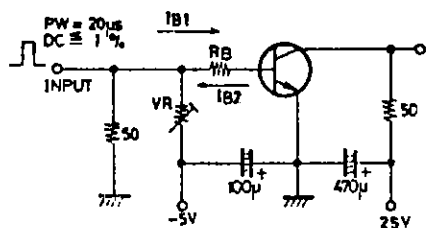
(Note) Mounted on ceramic board ($250\text{mm}^2 \times 0.8\text{mm}$)**Electrical Characteristics** at $T_a=25^\circ\text{C}$

		min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)50\text{V}, I_E=0$		(-)100	nA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=(-)4\text{V}, I_C=0$		(-)100	nA
DC Current Gain	h_{FE1}	$V_{CE}=(-)2\text{V}, I_C=(-)100\text{mA}$	100*	560*	
	h_{FE2}	$V_{CE}=(-)2\text{V}, I_C=(-)1.5\text{A}$	40		
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$	150		MHz
Output Capacitance	c_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$	(22)12		pF

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* The 2SB1123/2SD1623 are classified by 100mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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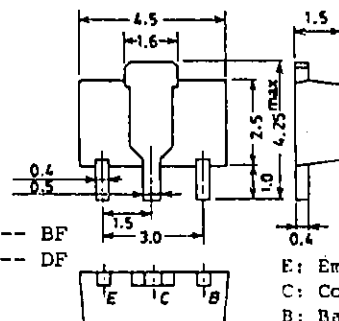
Switching Time Test Circuit

$$20I_{B1} = -20I_{B2} = I_C = 500\text{mA}$$

(For PNP, the polarity is reversed.)

Unit (Resistance : Ω , Capacitance : F)**Package Dimensions 2038**

(unit:mm)

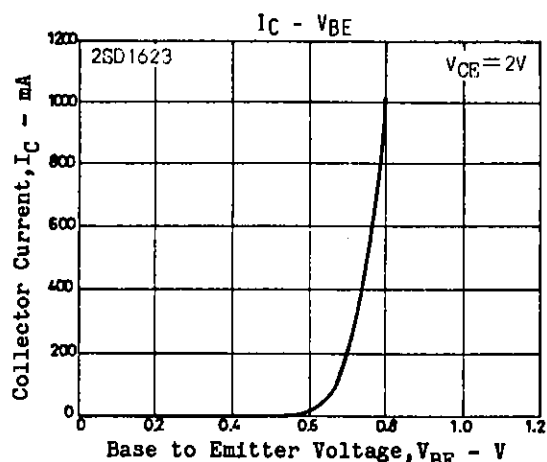
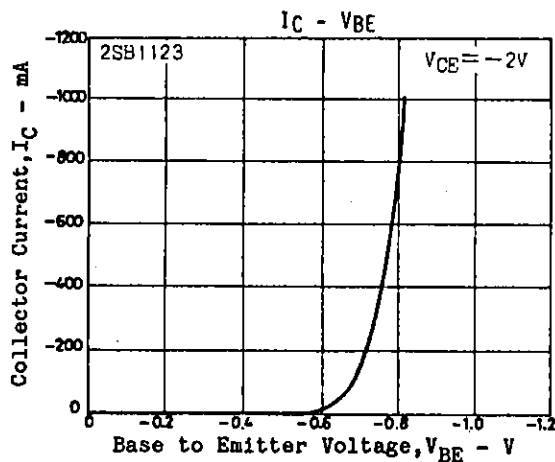
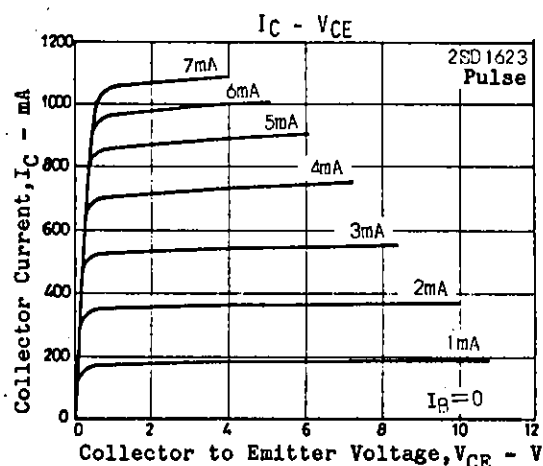
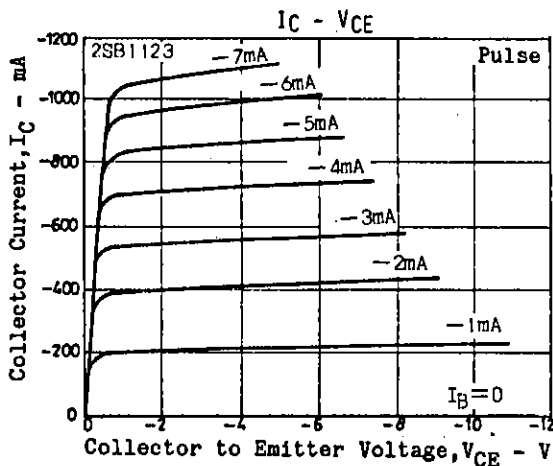
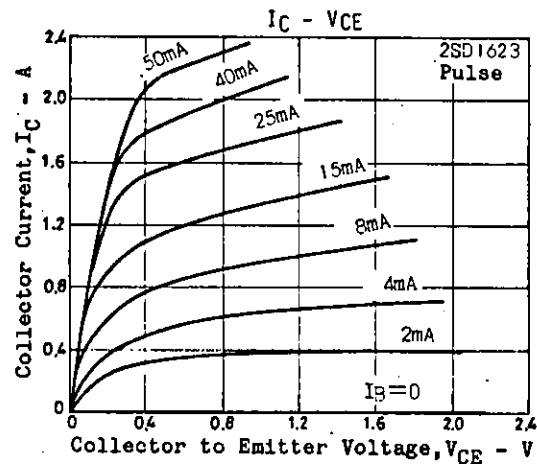
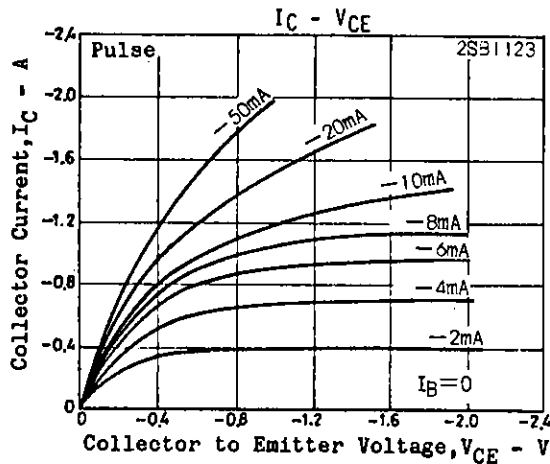
Marking: 2SB1123 -- BF
2SD1623 -- DFE: Emitter
C: Collector
B: BaseSANYO: PCP
(Bottom View)**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

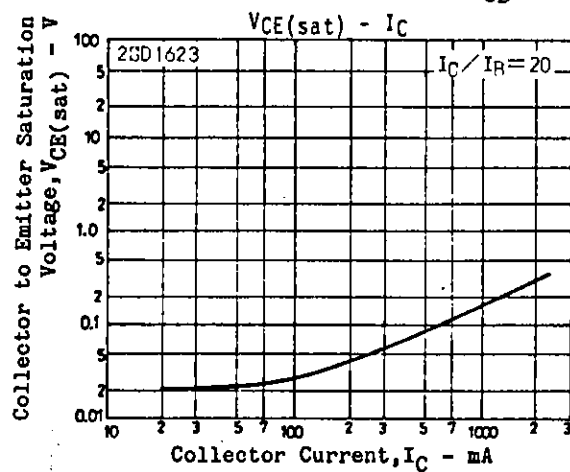
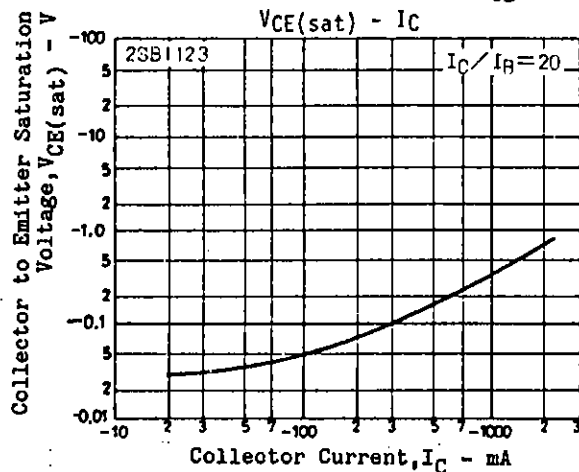
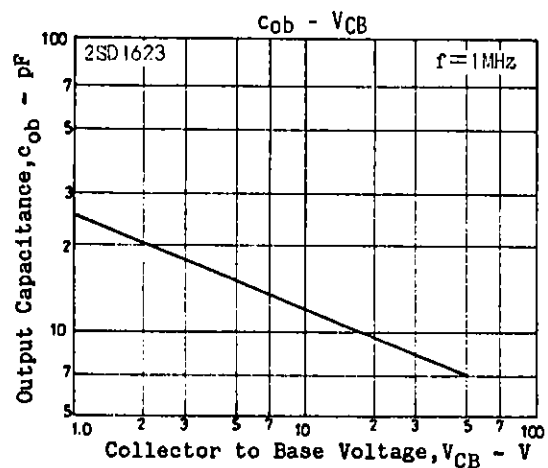
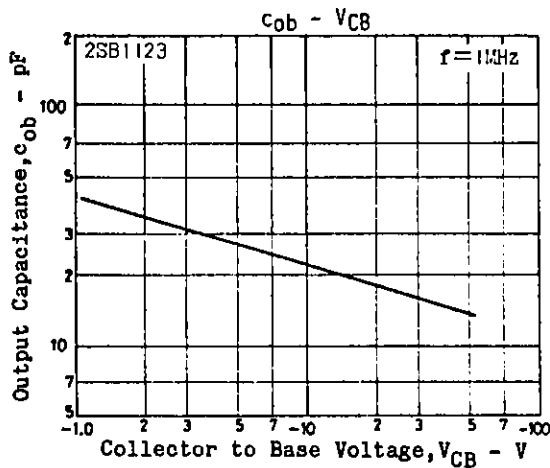
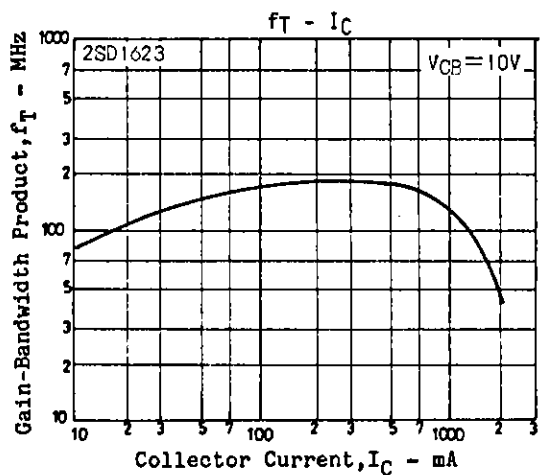
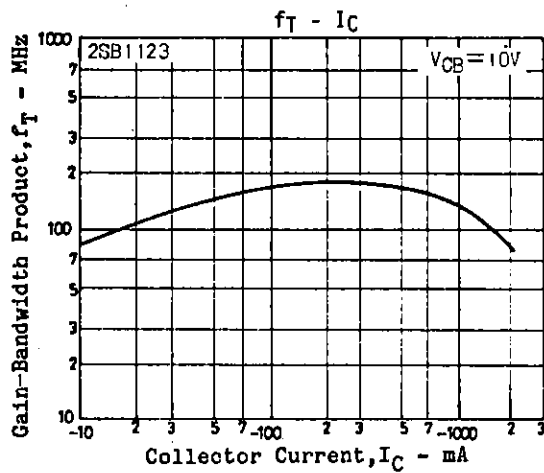
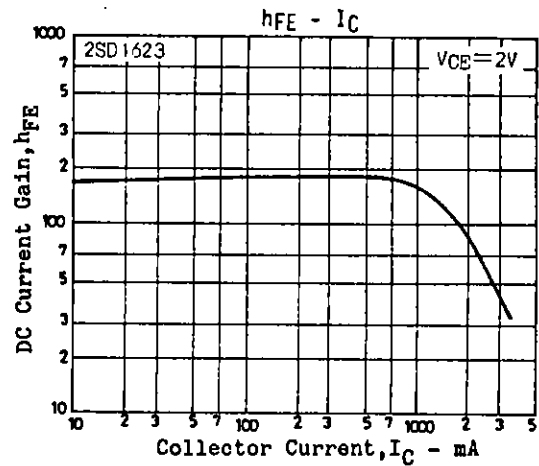
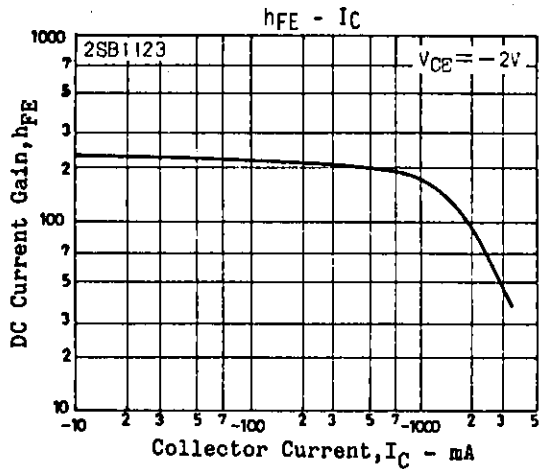
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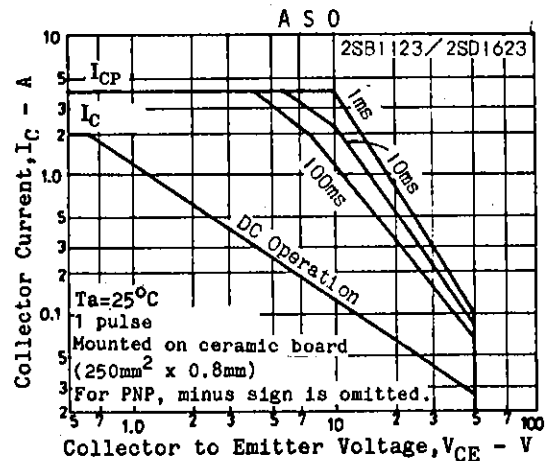
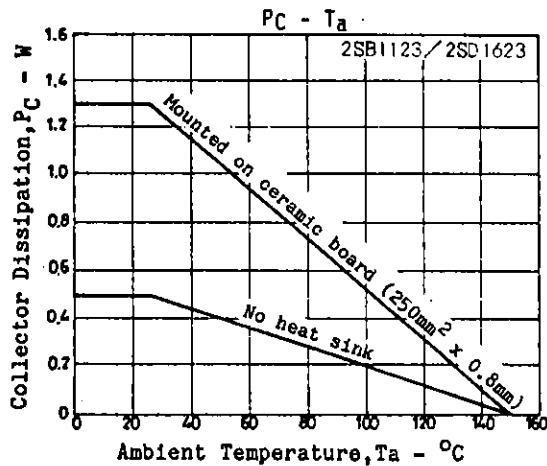
2SB1123/2SD1623

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			min	typ	max	unit
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-0.3)(-0.7)		V
				0.15	0.4	
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-)0.9(-)1.2		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.	(60)60			ns
Storage Time	t_{stg}	"	(450)550			ns
Fall Time	t_f	"	(30)30			ns







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